MSKSEMI















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Broduct data sheet



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VOLTAGE RANGE 45 to 200 Volts CURRENT 10.0Ampere



SMB

FEATURES

- * Ideal for surface mount applications
- * Easy pick and place
- * Built-in strain relief
- * Low forward voltage drop

MECHANICAL DATA

- * Case: Molded plastic
- * Epoxy: UL 94V-0 rate flame retardant
- * Metallurgically bonded construction
- * Polarity: Color band denotes cathode end
- * Mounting position: Any * Weight: 0.093 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25°C ambient temperature unless otherwies specified. Single phase half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

P/N(MARK	SS1045B	SS1060B	SS10100B	SS10150B	SS10200B	UNITS
Maximum Recurrent Peak Reverse Voltage	45	60	100	150	200	V
Maximum RMS Voltage	32	42	70	105	140	V
Maximum DC Blocking Voltage	45	60	100	150	200	V
Maximum Average Forward Rectified Current		•			1	
See Fig. 1		10.0				Α
Peak Forward Surge Current, 8.3 ms single half sine-way	е					
superimposed on rated load (JEDEC method)		175				Α
Maximum Instantaneous Forward Voltage at 10.0A	0.55	0.7	0.85	0.9	92	V
Maximum DC Reverse Current Ta=25°C	0.	0.1 0.02			μА	
at Rated DC Blocking Voltage Ta=125°C	5	5 2			mA	
Typical Junction Capacitance (Note1)		400				pF
Typical Thermal Resistance R JA (Note 2)		16				°C/W
Operating Temperature Range T _J	-	55 to +150				°C
Storage Temperature Range Tstg		-55 to +150				°C

NOTES:

- 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
- 2. Thermal Resistance Junction to Lead.

RATING AND CHARACTERISTIC CURVES (SS1045B THRU SS10200B)

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

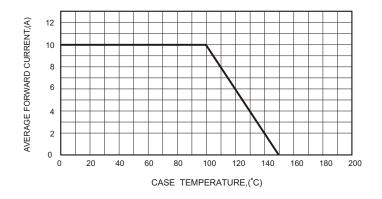


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

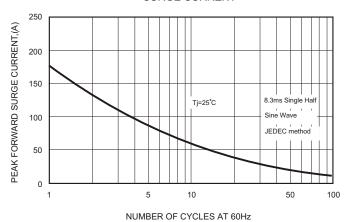


FIG.4-TYPICAL JUNCTION CAPACITANCE

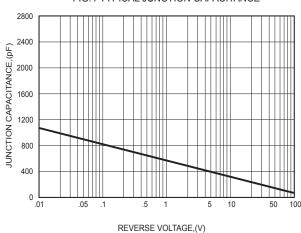


FIG.2-TYPICAL FORWARD

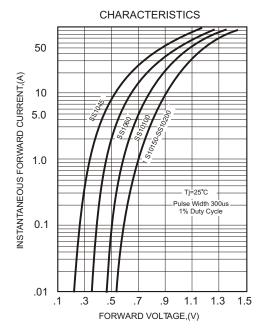
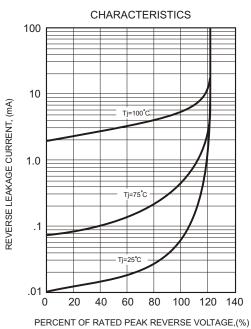


FIG.5 - TYPICAL REVERSE

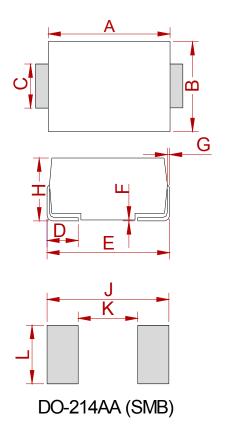












	Dimensions					
Ref.	Ref. Millimeters		Inches			
	Min.	Max.	Min.	Max.		
Α	4.25	4.75	0.167	0.187		
В	3.30	3.94	0.130	0.155		
С	1.85	2.21	0.073	0.087		
D	0.76	1.52	0.030	0.060		
Е	5.08	5.59	0.200	0.220		
F	0.051	0.203	0.002	0.008		
G	0.15	0.31	0.006	0.012		
Н	2.11	2.44	0.083	0.096		
J	6.80		0.270			
K		2.60		0.100		
L	2.40		0.090			

REEL SPECIFICATION

P/N	PKG	QTY
SS1045B THRU SS10200B	SMB	3000



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